Quad 2-Input AND Gate

The MC74VHC08 is an advanced high speed CMOS 2-input AND gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 4.3 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2.0 \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

- Chip Complexity: 24 FETs or 6 Equivalent Gates
- Pb-Free Packages are Available*

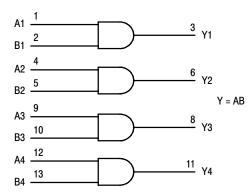


Figure 1. Logic Diagram

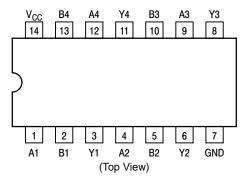


Figure 2. Pinout: 14-Lead Packages

Techniques Reference Manual, SOLDERRM/D.



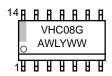
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MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A





TSSOP DT SUFFIX CASE 948G





SOEIAJ-14 M SUFFIX CASE 965



A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week

G or ■ = Pb–Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

Inputs		Output
Α	В	Υ
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

November, 2005 - Rev. 6

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting

MAXIMUM RATINGS

Symbol	Parameter	r	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{in}	DC Input Voltage		-0.5 to +7.0	V
V _{out}	DC Output Voltage		-0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current		-20	mA
I _{OK}	Output Diode Current		±20	mA
l _{out}	DC Output Current, per Pin		±25	mA
I _{CC}	DC Supply Current, V _{CC} and GI	ND Pins	±50	mA
P _D	Power Dissipation in Still Air,	SOIC Packages [†] TSSOP Package [†]	500 450	mW
T _{stq}	Storage Temperature		-65 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	1	Max	Unit
V _{CC}	DC Supply Voltage	2.0)	5.5	V
V _{in}	DC Input Voltage	0		5.5	V
V _{out}	DC Output Voltage	0		V _{CC}	V
T _A	Operating Temperature	-40)	+85	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 3.3 \text{ V} \pm V_{CC} = 5.0 \text{ V} \pm 0.00 \pm 0.00$	0.3 V 0 0.5 V 0		100 20	ns/V

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS

		Voc	V _{CC}	T,	$T_A = 25^{\circ}C$ $T_A = -40 \text{ to } 85^{\circ}C$		$T_A = -40 \text{ to } 85^{\circ}\text{C}$		
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V_{IH}	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} x 0.7			1.50 V _{CC} x 0.7		٧
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V _{CC} x 0.3		0.50 V _{CC} x 0.3	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4.0 \text{ mA}$ $I_{OH} = -8.0 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}}$ $I_{\text{OL}} = 4.0 \text{ mA}$ $I_{\text{OL}} = 8.0 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44	
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	5.5			2.0		20.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

				T _A = 25°C			T _A = - 40 to 85°C		
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A or B to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		6.2 8.7	8.8 12.3	1.0 1.0	10.5 14.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		4.3 5.8	5.9 7.9	1.0 1.0	7.0 9.0	
C _{in}	Maximum Input Capacitance				4	10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 1)	18	pF

C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per gate). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_{r} = t_{f} = 3.0$ ns, $C_{L} = 50$ pF, $V_{CC} = 5.0$ V)

		T _A =	25°C	
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

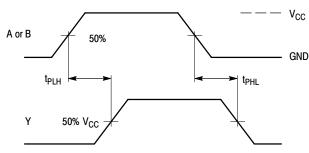
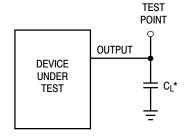


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

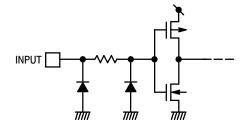


Figure 5. Input Equivalent Circuit

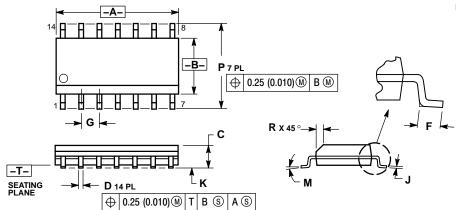
ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHC08DR2	SOIC-14	2500 Units / Tape & Reel
MC74VHC08DR2G	SOIC-14 (Pb-Free)	2500 Units / Tape & Reel
MC74VHC08DTR2	TSSOP-14*	2500 Units / Tape & Reel
MC74VHC08DTR2G	TSSOP-14*	2500 Units / Tape & Reel
MC74VHC08MEL	SOEIAJ-14	2000 Units / Tape & Reel
MC74VHC08MELG	SOEIAJ-14 (Pb-Free)	2000 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb–Free.

PACKAGE DIMENSIONS

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE G**



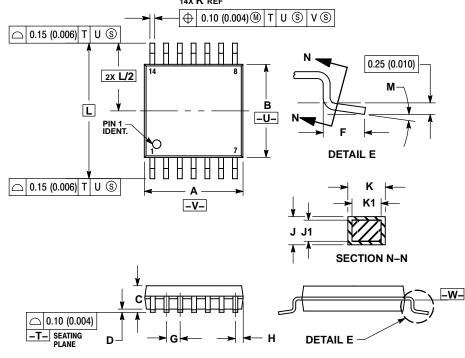
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- FER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27 BSC		0.050	BSC	
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
М	0 °	7°	0 °	7°	
Р	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.010	

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE A**



- OTES:

 1. DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

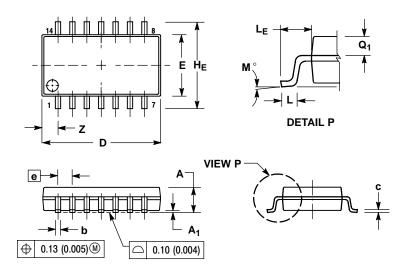
 3. DIMENSION A DOES NOT INCLUDE MOLD
 FLASH, PROTRUSIONS OR GATE BURRS.
 MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE
- DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08
 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252	BSC
М	0 °	8 °	0°	8 °

PACKAGE DIMENSIONS

SOEIAJ-14 **M SUFFIX** CASE 965-01 **ISSUE A**



NOTES:

- 1. DIMENSIO Y14.5M, 1982. DIMENSIONING AND TOLERANCING PER ANSI
- 114.3M, 1962.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE
 MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (0.000) PER SIDE.
 4. TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.
 5. THE LEAD WIDTH DIMENSION (b) DOES NOT
 INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		TERS INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
Α ₁	0.05	0.20	0.002	0.008
q	0.35	0.50	0.014	0.020
O	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
e	1.27	BSC	0.050 BSC	
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0°	10°
ą	0.70	0.90	0.028	0.035
Z		1.42		0.056

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